M.E.T.C.E Examination 2017 (1st year,1st Semester)

PHYSICAL ELECTRONICS

The figures in margin indicate full marks. All the questions must be answered in one place. The answers should be precise.

Answer any five questions and carry equal marks

Full Ma	arks:100	Time: Three hours
• •	efine Hall mobility. Explain how drift mobility deperameters?	ends on material 6
	hat is the Hall voltage? How is it related to drift mobility is used for material characterisation?	nobility? How Hall 8
	nat is a compensated semiconductor? Obtain its I pression.	Hall Coefficient 6
Q. 2 (a)	Describe the different recombination processes	in semiconductors
(b)	Obtain the following; (i) Recombination life time, (ii) Absorption probabilities of electron and hole for Schokley-Read —Hall(SRH)I recombination.	(8+7) es,
Q.3 (a)	Obtain Einstein relation. Discuss the validity cond this relation.	itions for 6
	Derive the diffusion equation for holes . What is t the relation?	he significance of 8
(c) [Deduce the excess carrier decay equation.	6

	plain the concept of quasi Fermi energy. How is it significant taterials?	o 6
(b) II	ustrate the different carrier generation mechanisms.	6
S	escribe Auger band to band recombination. Give its relevance emiconductor optical devices. Compare it with band to band ecombination for direct band semiconductor.	e to
	•	8
Q. 5 (a) E	educe the expression for the following;	
(i) (ii)	Surface recombination velocity Band to band recombination coefficient	20
· · · -	Explain the different types of traps in semiconductors. How test semiconducting properties?	hey
		10
	Discuss the effect of different scattering mechanisms at low a	nd high
	temperatures	10
	btain the Hall coefficient in a semiconductor using the Boltzm quation in the presence of electric and magnetic fields.	ann 20
•	te short note on any four	5x4=20
-	te short note on any four Boltzmann Transport Equation Carrier generation Measurement of Hall coefficient	5x4=20